**TENTATIVE** 

TOSHIBA Photocoupler GaAlAs Ired & Photo-Diode Array

# **TLP191B**

**Telecommunication Programmable Controllers** Mos Gate Driver MOS FET Gate Driver

The TOSHIBA mini flat coupler TLP191B is a small outline coupler, suitable for surface mount assembly.

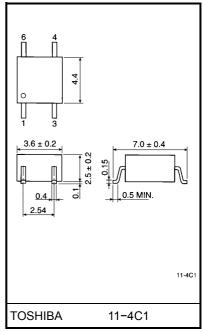
The TLP191B consists of a GaAlAs light emitting diode, optically coupled to a series connected photo diode array with shunt resistor which is suitable for MOS FET gate drive.

Open voltage: 7.0V(min.) Short current: 24.0 µA (min.) Isolation voltage: 2500 Vrms (min.) UL recognized: UL1577, file no. E67349

### **Maximum Ratings (Ta = 25°C)**

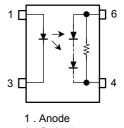
Characteristic		Symbol	Rating	Unit
	Forward current	l <sub>F</sub>	50	mA
LED	Forward current derating (Ta ≥ 25°C)	ΔI <sub>F</sub> / °C	-0.5	mA / °C
	Pulse forward current (100µs pulse, 100 pps)	I <sub>FP</sub>	1	А
	Reverse voltage	V <sub>R</sub>	3	V
	Junction temperature	Тj	125	°C
	Forward current	I <sub>FD</sub>	50	μΑ
Detector	Reverse voltage	$V_{RD}$	10	V
	Junction temperature	Tj	125	°C
Storage ter	nperature range	T <sub>stg</sub>	-55~125	°C
Operating temperature range		T <sub>opr</sub>	-40~80	°C
Lead soldering temperature (10s)		T <sub>sol</sub>	260	°C
Isolation voltage (AC, 1 min., R.H. ≤ 60%) (Note)		BVS	2500	Vrms

Unit in mm



Weight: 0.09 g

### Pin Configuration(top view)



- 3. Cathode
- 4 . Cathode
- 6 . Anode

(Note) Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4 and 6 shorted together.

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## **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Forward current	IF	_	20	25	mA
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

# Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.2	1.4	1.7	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 3 V	_	_	10	μA
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	_	30	60	pF
	Forward voltage	$V_{FD}$	I <sub>FD</sub> = 10 μA	_	7	_	V
Detector	Reverse current	I <sub>RD</sub>	V <sub>RD</sub> = 10 V	_	7	_	μA
	Capacitance (anode to cathode)	C <sub>TD</sub>	V = 0, f = 1 MHz	ı	-	_	pF

## **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Open voltage	V <sub>OC</sub>	I <sub>F</sub> = 20 mA	7	8	_	٧
Short current	I <sub>SC</sub>	I <sub>F</sub> = 20 mA	24	40	_	μA

### **Isolation Characteristics (Ta = 25°C)**

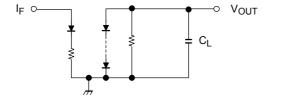
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V <sub>S</sub> = 0, f = 1 MHz	_	8.0	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	2500	_	_	Vrms
Isolation voltage	BV <sub>S</sub> AC, 1 second in oil	AC, 1 second in oil	_	5000	_	VIIIIS
		DC, 1 minute in oil	_	5000	_	Vdc

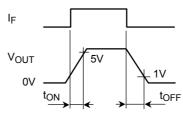
### **Switching Characteristics (Ta = 25°C)**

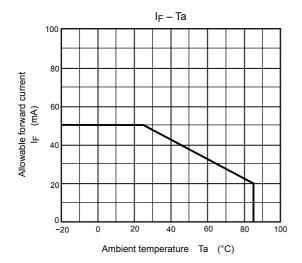
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Turn-on time	t <sub>ON</sub>	I <sub>F</sub> = 20mA, C <sub>L</sub> = 1000 pF	_	0.2	_	ms
Turn-off time	toff	(Fig.1)	-	3		ms

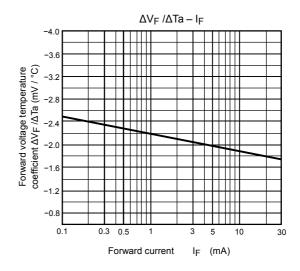
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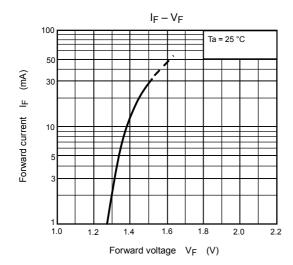
Fig. 1 Switching time test circuit

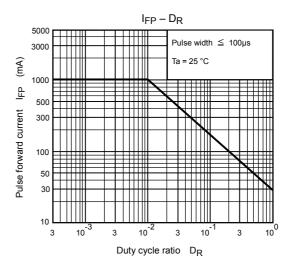


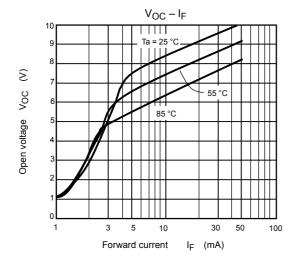


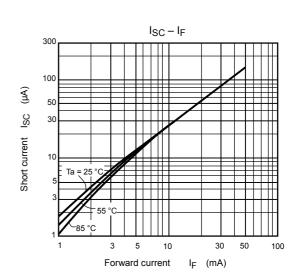












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